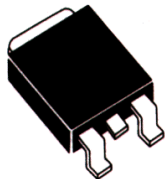




CJD44H11 NPN
CJD45H11 PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

DPAK **POWER!**™



DPAK CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD44H11, CJD45H11 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for switching and power amplifier applications.

MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNITS
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	8.0	A
Peak Collector Current	I _{CM}	16	A
Power Dissipation (T _C =25°C)	P _D	20	W
Power Dissipation (T _A =25°C)	P _D	1.75	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JC}	6.25	°C/W
Thermal Resistance	θ _{JA}	71.4	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CES}	V _{CE} =80V			10	μA
I _{EBO}	V _{EB} =5.0V			50	μA
BV _{CEO}	I _C =30mA	80			V
V _{CE(SAT)}	I _C =8.0A, I _B =400mA			1.0	V
V _{BE(SAT)}	I _C =8.0A, I _B =800mA			1.5	V
h _{FE}	V _{CE} =1.0V, I _C =2.0A	60			
h _{FE}	V _{CE} =1.0V, I _C =4.0A	40			
f _T	V _{CE} =10V, I _C =500mA, f=20MHz (CJD44H11)		60		MHz
f _T	V _{CE} =10V, I _C =500mA, f=20MHz (CJD45H11)		50		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=0.1MHz (CJD44H11)		120		pF
C _{ob}	V _{CB} =10V, I _E =0, f=0.1MHz (CJD45H11)		220		pF
t _d + t _r	I _C =5.0A, I _{B1} =500mA (CJD44H11)		320		ns
t _d + t _r	I _C =5.0A, I _{B1} =500mA (CJD45H11)		150		ns

All dimensions in inches (mm).



- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR